

Cellular
Power Amplifier

Broadband GaN
Power Amplifier

Amplifier System



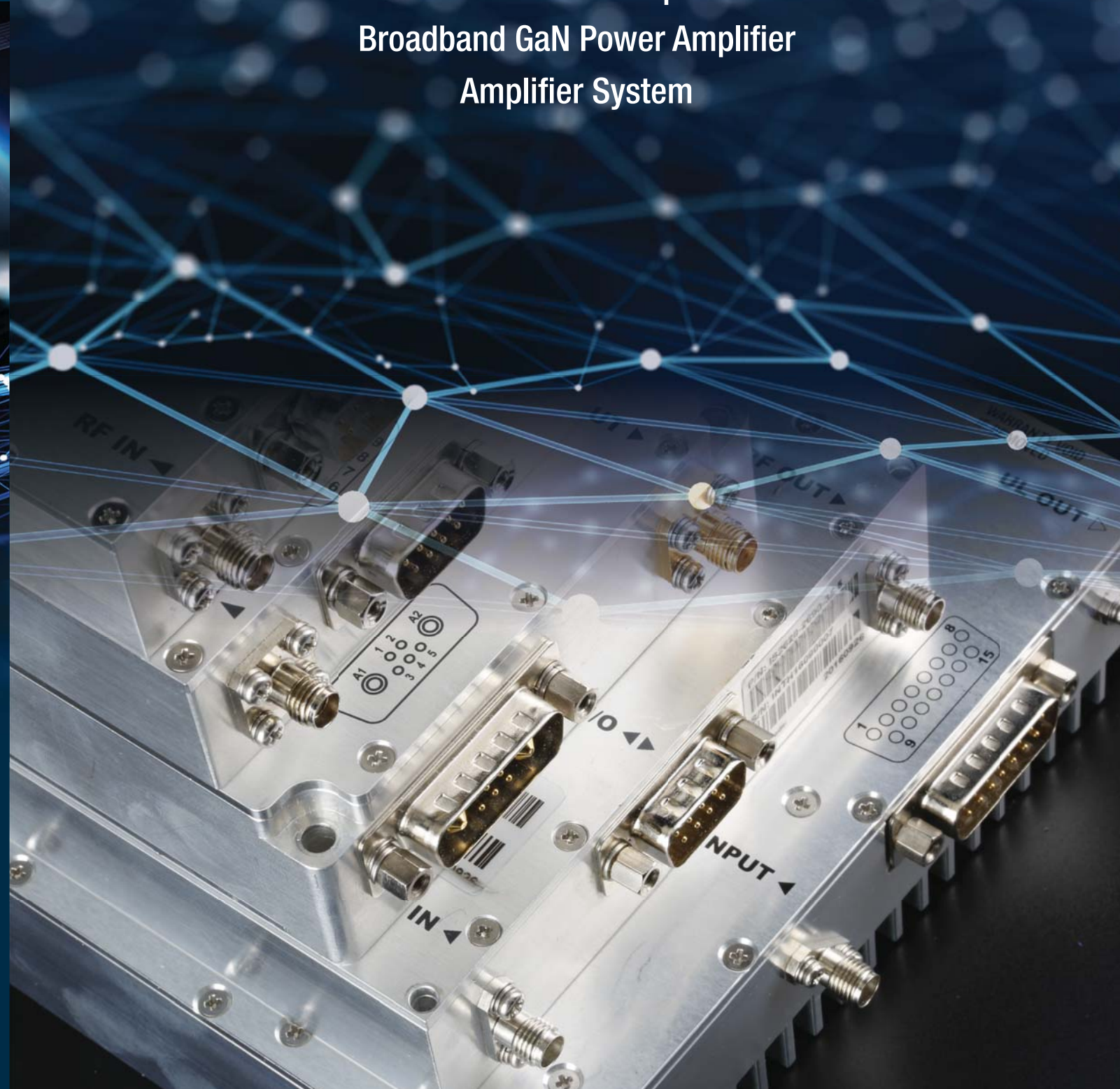
INSPOWER™

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Broadband GaN Power Amplifier
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PRODUCT

Cellular Power Amplifiers

Inspower's Cellular Power Amplifiers are ideal for customers involved with DAS systems, BTS solutions and RF repeaters, which require highly linear products with low distortion and low EVM. They are well-suited for LTE, Cellular, WCDMA, GSM, PCS and UMTS systems. These products are designed in combination with various technologies, symmetrical and asymmetrical Doherty configurations to achieve high efficiency, and feed-forward, analog pre-distortion and other linearization techniques to achieve high linearity. These Products are used by leading global DAS manufacturers and mobile network companies.

Model Number	Frequency Start(MHz)	Frequency Stop(MHz)	Linear Pout(Watt)	Linear Pout(dBm)	Gain (dB)	Voltage (Volts)	Current (Amps)	Two-tone IMD(dBm)	Size (mm)	Application
ILA1015	450	512	6.3	38	45	28	2.0	-36	180 x 150 x 30	Tetra / P25
ILA1037	617	652	2.5	34	41	28	1.1	-20	120 x 110 x 25	LTE 600
ILA1001	728	757	2.5	34	41	28	1.1	-20	120 x 110 x 25	LTE 700
ILA1018	752.5	762.5	20	43	46	28	5	-12	173 x 108 x 25.4	QAM
ILA1002	758	803	2.5	34	41	28	1.1	-18	120 x 110 x 25	APT LTE 700
ILA1003	791	821	2.5	34	41	28	1.1	-20	120 x 110 x 25	LTE 800
ILA1004	862	894	2.0	33	41	28	1.1	-20	120 x 110 x 25	Cellular/LTE
ILA1005	925	960	2.0	33	41	28	1.4	-38	130 x 120 x 30	EGSM
ILA1006	1805	1880	3.5	35.5	43	28	1.6	-32	130 x 120 x 30	DCS
ILA1007	1930	2000	3.5	35.5	43	28	1.45	-20	120 x 110 x 30	PCS/LTE
ILA1026	2110	2180	3.5	35.5	43	28	1.4	-15	130 x 120 x 25	UMTS/AWS
ILA1020 19	2110	2180	10	40	48	28	2.5	-	170 x 120 x 25	UMTS/AWS
ILA1021	2110	2180	25	44	52	28	5	-	170 x 145 x 25	UMTS/AWS
ILA1025 24	2110	2180	50	47	55	28	7	-	170 x 145 x 25	UMTS/AWS
ILA1009	2345	2360	4.0	36	45	28	1.4	-20	120 x 110 x 25	WCS
ILA1010	2620	2690	3.5	35.5	45	28	1.4	-15	120 x 110 x 25	LTE 2600
ILA1011	2496	2690	5.0	37	45	28	1.6	-15	170 x 150 x 35	LTE TDD
ILA1030	2496	2690	20	43	60	28	5	-	170 x 145 x 25	LTE TDD
INS1912	1930	1990	1	30	26	28	0.4	-	45 x 14 x 7	PCS
INS2110	2110	2170	1	30	24	28	0.5	-	45 x 14 x 7	UMTS

Band Specific Amplifiers

Band Specific Amplifiers are the best solution to reduce cost and improve linearity and efficiency performance over a narrower frequency range than broadband amplifiers. Although designed with LDMOS, GaN and GaAs FET, LDMOS FET has a priority to optimize cost and performance. Output isolator can also be installed.

Model Number	Frequency Start(MHz)	Frequency Stop(MHz)	Pout (Watts)	Gain (dB)	Voltage (Volts)	Current (Amps)	Size (mm)	Device Type
INS2008	600	800	25	44	28	3	150 x 90 x 25	LDMOS
INS2001	800	1000	50	48	27	5.5	110 x 95 x 22	LDMOS
INS2017	860	960	100	50	27	12	140 x 125 x 25	LDMOS
INS2032	900	1300	80	49	28	10	200 x 90 x 28	GaN
INS2009	1500	1700	50	49	24	5.5	110 x 95 x 22	LDMOS
INS2002	1800	2000	50	48	27	5.5	110 x 95 x 22	LDMOS
INS2004	1800	2000	100	50	27	12	150 x 135 x 25	LDMOS
INS2010	2100	2300	50	48	27	5.5	110 x 95 x 22	LDMOS
INS2006	3400	3600	4	19	7	3	71.12 x 38.1 x 13.97	GaAs
INS2007	3400	3600	15	46.8	28	4	200 x 150 x 37	LDMOS
INS2018	3400	3600	40	51	28	8.5	200 x 150 x 37	LDMOS
INS2005	3400	3700	100	58	28	22	150 x 170 x 28	LDMOS
INS2028	4400	5000	3	34	12	1.5	90 x 90 x 20	GaN
INS2011	4400	5000	20	46.5	10	8.5	156 x 82 x 20	GaN
INS2012	4400	5000	20	46.5	28	2.5	156 x 82 x 20	GaN
INS2013	5070	5270	10	30	28	3	180 x 75 x 25	GaN
INS2014	6860	7060	10	30	28	3.5	180 x 75 x 25	GaN



Broadband Amplifiers

Inspower's Broadband amplifiers are available in frequencies between 1 MHz and 8GHz with power levels up to 200Watts. Using the latest solid-state technologies such as GaN, LDMOS and GaAs, our expert engineers cater to a wide range product lines. The table below shows some of the popular models that we have already developed. And the models is being still extended and upgraded by continuous R&D activities to satisfy customer requirements.

Model Number	Frequency Start(MHz)	Frequency Stop(MHz)	Pout (Watts)	Gain (dB)	Voltage (Volts)	Current (Amps)	Size (mm)	FWD Detector	Device Type
INS3001	1	100	50	46	28	7	162.56 x 86.36 x 25.4		LDMOS
INS3024	20	520	100	50	28	12	134.62 x 63.5 x 26.67		LDMOS
INS3017	20	520	100	50	28	12	152.4 x 68.58 x 26.67	O	LDMOS
INS3004	20	530	12	42	28	1	85 x 85 x 26	O	GaN
INS3018	20	530	100	50	28	8.5	185 x 80 x 27	O	LDMOS
INS3005	20	1000	100	58	28	9	162.56 x 86.36 x 27		GaN
INS3012	800	2170	12	42	28	2.5	170 x 70 x 22		GaN
INS3045	20	2500	10	40	24	2.1	100 x 85 x 20		GaN
INS3006	500	2500	50	46	28	6	200 x 90 x 28	O	GaN
INS3035	500	2500	100	50	28	12	185 x 90 x 22		GaN
INS3008	500	2500	100	49	28	14	200 x 140 x 27	O	GaN
INS3037	700	2700	100	50	28	14	185 x 90 x 22		GaN
INS3020	1000	3000	50	40	28	7	170 x 70 x 30		GaN
INS3026	2500	6000	35	46	28	10	180 x 90 x 20		GaN
INS3078	3000	6000	35	46	28	9	170 x 70 x 30		GaN
INS3072	2000	6000	100	50	28	24	230 x 120 x 25		GaN

Amplifier Systems

Inspower designs and manufactures High Power RF and Microwave Systems for use in test & measurement, communications and other types of systems. The systems we make typically contain high power amplifiers, heat sink / fan, power supply and Breaker / switch. Options can include voltage variable attenuators, circulators, forward / reflected ports and other controls and monitoring.

Model Number	Frequency Start(MHz)	Frequency Stop(MHz)	Pout (Watts)	Gain (dB)	Voltage (VAC)	Pd (Watts)	Size (inch)	Device Type
INS5001	20	1000	50	46	100 - 240	700	R2U	GaN
INS5002	20	1000	100	49	100 - 240	750	R3U	GaN
INS5003	500	2500	50	46	100 - 240	250	R2U	GaN
INS5004	500	2500	100	50	100 - 240	800	R3U	GaN
	1000	3000	100	49	100 - 240	1400	R5U	GaN
INS5006	2000	4000	50	46	100 - 240	400	R3U	GaN
INS5007	2500	6000	35	48	100 - 240	700	R3U	GaN